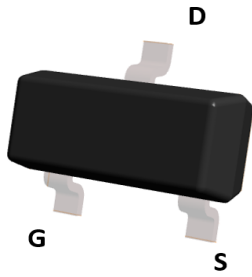
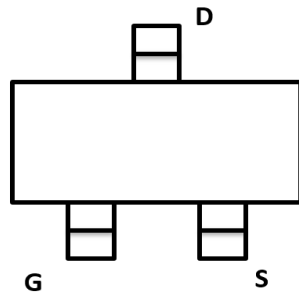


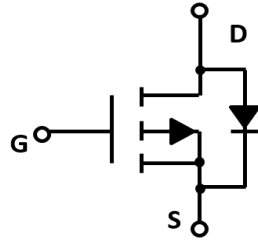
## P-Channel Enhancement Mode Field Effect Transistor



Top View



**SOT-23-3L**



### Product Summary

- $V_{DS}$  -30V
- $I_D$  -4.1A
- $R_{DS(ON)}$  (at  $V_{GS}=-10V$ ) <55 mohm
- $R_{DS(ON)}$  (at  $V_{GS}=-4.5V$ ) <68 mohm

### General Description

- Trench Power LV MOSFET technology
- High density cell design for Low  $R_{DS(ON)}$
- High Speed switching

### Applications

- Battery protection
- Load switch
- Power management

### ■ Absolute Maximum Ratings ( $T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Maximum	Unit
Drain-source Voltage	$V_{DS}$	-30	V
Gate-source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current	$I_D$	$T_A=25^\circ C$ @ Steady State	-4.1
		$T_A=70^\circ C$ @ Steady State	-3.2
Pulsed Drain Current <sup>A</sup>	$I_{DM}$	-15	A
Total Power Dissipation @ $T_A=25^\circ C$	$P_D$	1.5	W
Thermal Resistance Junction-to-Ambient @ Steady State <sup>B</sup>	$R_{\theta JA}$	82	$^\circ C/W$
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55~+150	$^\circ C$

### ■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJL3407AL	F2	3407.	3000	30000	120000	7" reel



# YJL3407AL

## ■ Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
<b>Static Parameter</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =-250μA	-30			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-30V, V <sub>GS</sub> =0V, T <sub>C</sub> =25°C			-1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±20V, V <sub>DS</sub> =0V			±100	nA
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250μA	-1.0	-1.5	-2.4	V
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = -10V, I <sub>D</sub> =-4.1A		40	55	mΩ
		V <sub>GS</sub> = -4.5V, I <sub>D</sub> =-3.5A		53	68	
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =-4.1A, V <sub>GS</sub> =0V		-0.8	-1.2	V
Maximum Body-Diode Continuous Current	I <sub>S</sub>				-4.1	A
<b>Dynamic Parameters</b>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =-15V, V <sub>GS</sub> =0V, f=1MHZ		580		pF
Output Capacitance	C <sub>oss</sub>			98		
Reverse Transfer Capacitance	C <sub>rss</sub>			74		
<b>Switching Parameters</b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>GS</sub> =-10V, V <sub>DS</sub> =-15V, I <sub>D</sub> =-4.1A		6.8		nC
Gate Source Charge	Q <sub>gs</sub>			1.0		
Gate Drain Charge	Q <sub>gd</sub>			1.4		
Turn-on Delay Time	t <sub>D(on)</sub>	V <sub>GS</sub> =-10V, V <sub>DD</sub> =-15V, R <sub>L</sub> =15Ω, I <sub>D</sub> =-1A, R <sub>GEN</sub> =2.5Ω		14		ns
Turn-on Rise Time	t <sub>r</sub>			61		
Turn-off Delay Time	t <sub>D(off)</sub>			19		
Turn-off Fall Time	t <sub>f</sub>			10		

A. Pulse Test: Pulse Width ≤ 300us, Duty cycle ≤ 2%.

B. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch.

## ■ Typical Performance Characteristics

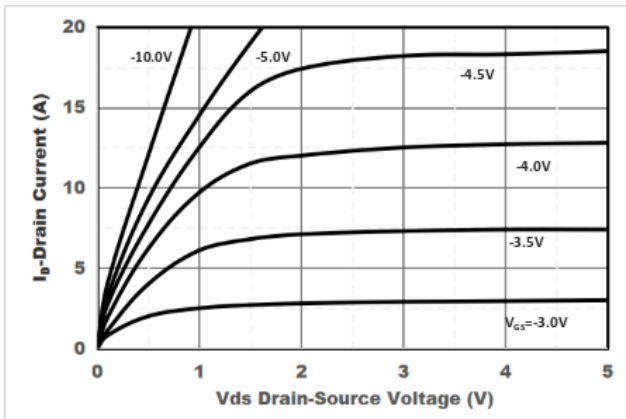


Figure1. Output Characteristics

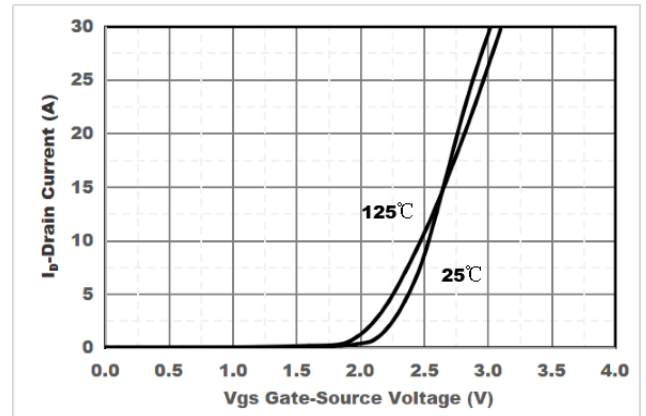


Figure2. Transfer Characteristics

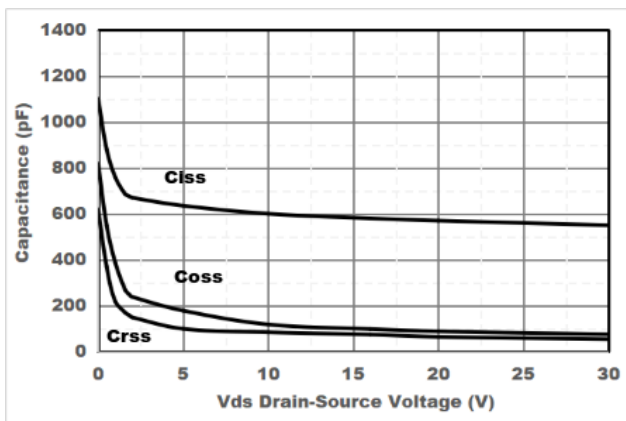


Figure3. Capacitance Characteristics

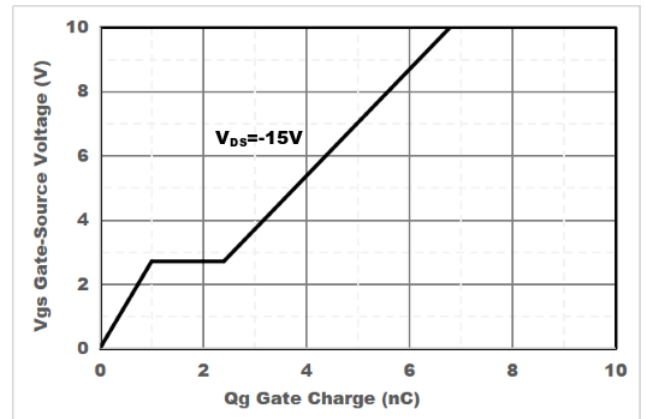


Figure4. Gate Charge

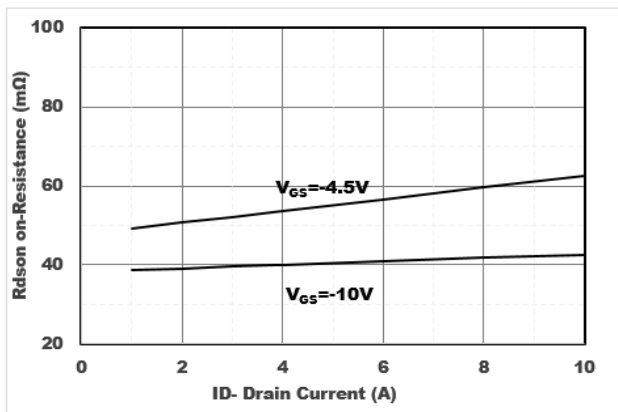


Figure5. Drain-Source on Resistance

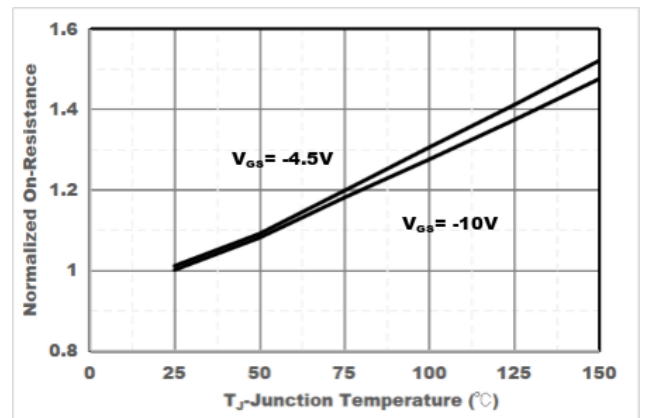


Figure6. Drain-Source on Resistance

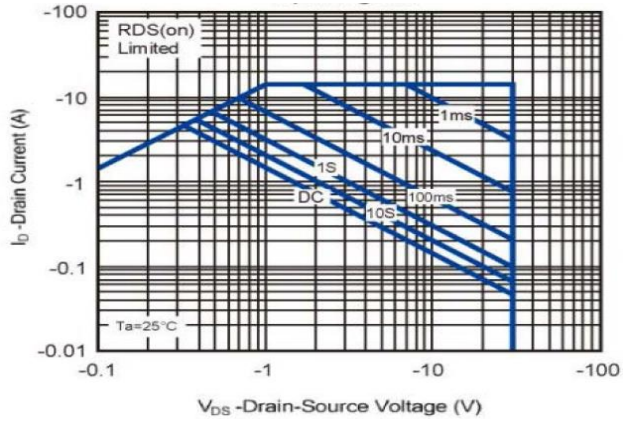


Figure7. Safe Operation Area

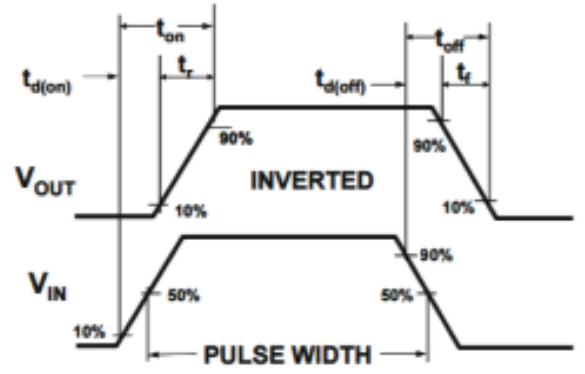
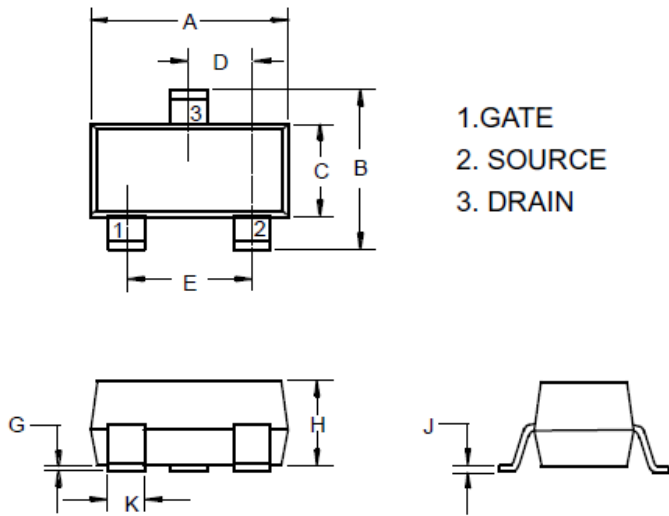


Figure8. Switching wave



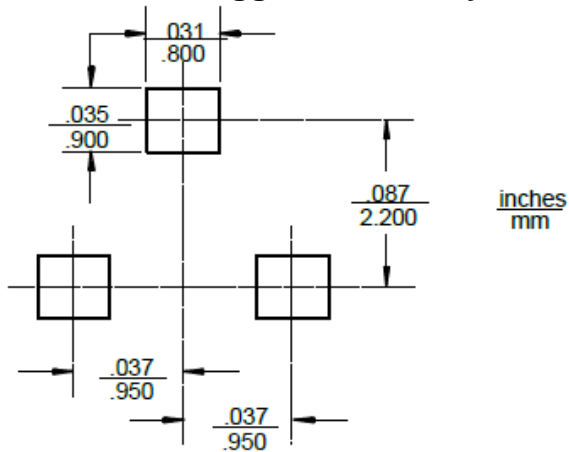
## ■ SOT-23-3L Package information

### SOT-23-3L



DIM	DIMENSIONS				NOTE
	INCHES		MM		
	MIN	MAX	MIN	MAX	
A	.113	.117	2.87	2.97	
B	.108	.112	2.75	2.85	
C	.061	.065	1.55	1.65	
D	.036	.038	.914	.965	
E	.073	.077	1.85	1.95	
G	.0016	.0039	.04	.100	
H	.044	.049	1.12	1.25	
J	.006	.007	.14	.17	
K	.013	.015	.34	.37	

## ■ SOT-23-3L Suggested Pad Layout





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